**Vishay Semiconductors** 

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Hyperfast Rectifier, 60 A FRED Pt<sup>®</sup> Gen 5



PRIMARY CHARACTERISTICS								
I <sub>F(AV)</sub>	60 A							
V <sub>R</sub>	1200 V							
V <sub>F</sub> at I <sub>F</sub> at 125 °C	2.1 V							
t <sub>rr</sub>	30 ns							
T <sub>J</sub> max.	175 °C							
Package	TO-247AD 2L							
Circuit configuration	Single							

## **FEATURES**

- Hyperfast and optimized Q<sub>rr</sub>
- · Best in class forward voltage drop and switching losses trade off
- · Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- AEC-Q101 qualified, meets JESD 201 class 1A whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

## **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant.

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

### **MECHANICAL DATA**

#### Case: TO-247AD 2L

Molding compound meets UL 94 V-0 flammability rating Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V <sub>RRM</sub>		1200	V						
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 101 °C, D = 0.50	60							
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_C = 45$ °C, $t_p = 10$ ms, sine wave	370	А						
Repetitive peak forward current	I <sub>FRM</sub>	T <sub>C</sub> = 101 °C, D = 0.50, f = 20 kHz	120							
Operating junction and storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C						

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER	MIN.	TYP.	MAX.	UNITS						
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	1200	-	-					
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 60 A	-	2.6	3.3	V				
Forward voltage		I <sub>F</sub> = 60 A, T <sub>J</sub> = 125 °C	-	2.1	-					
Reverse leakage current	1	$V_{R} = V_{R}$ rated	-	-	50					
Reverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA				
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	32	-	pF				
Series inductance	L <sub>S</sub>	Measured to lead 5 mm from package body	-	8	-	nH				

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS				
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt =	100 A/ $\mu$ s, V <sub>R</sub> = 30 V	-	30	-				
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	120	-	ns			
		T <sub>J</sub> = 125 °C		-	170	-				
Deals recovery everyont	1	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 40 A dI <sub>F</sub> /dt = 600 A/µs	-	17	-	A			
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm R} = 400 \text{ V}$	-	32	-				
Daviera a seconda a barra	0	T <sub>J</sub> = 25 °C		-	970	-	nC			
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	2950	-				
Deverse receiver time		T <sub>J</sub> = 25 °C		-	90	-	ns			
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	130	-				
Poole recovery ourrent		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 60 A dI <sub>F</sub> /dt = 1000 A/µs	-	32	-	A nC			
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm R} = 800  {\rm V}$	-	53	-				
Deverse we example the second	0	T <sub>J</sub> = 25 °C		-	1570	-				
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	4300	-	nc			

THERMAL - MECHANICAL SPECIFICATIONS											
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS					
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	0.4	°C/W					
Weight			-	5.5	-	g					
Weight			-	0.2	-	oz.					
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)					
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C					
Marking device		Case style: TO-247AD 2L	E5PX6012LH								

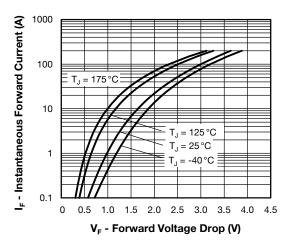


Fig. 1 - Typical Forward Voltage Drop Characteristics

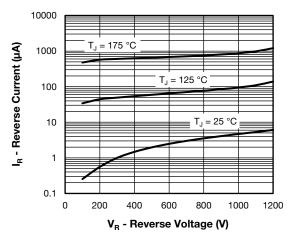
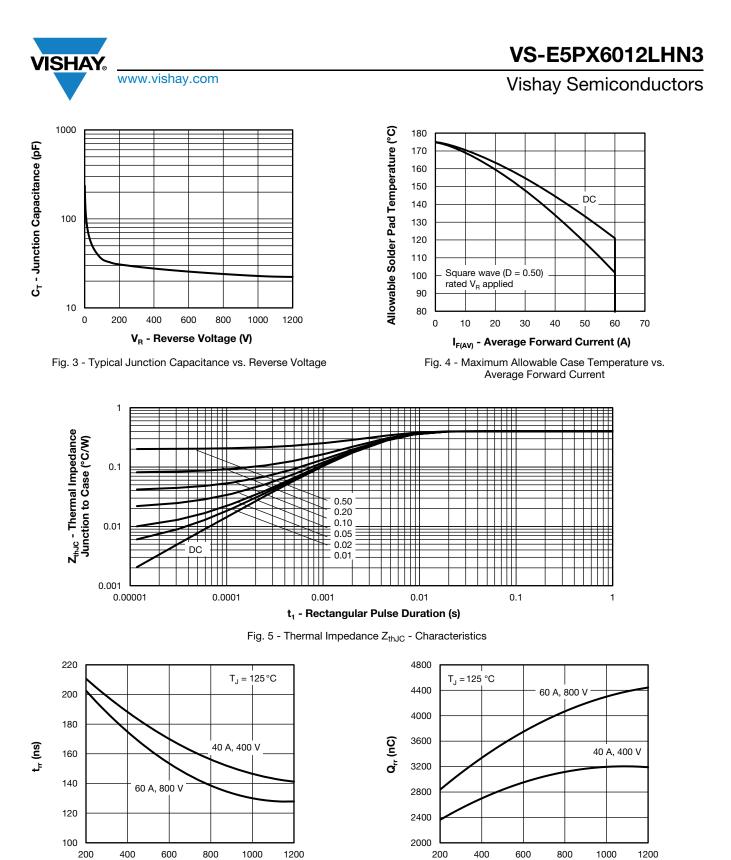


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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dl<sub>F</sub>/dt (A/μs)

Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

Fig. 7 - Typical Stored Charge vs.  $dI_F/dt$ 

dl<sub>F</sub>/dt (A/µs)

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# VS-E5PX6012LHN3

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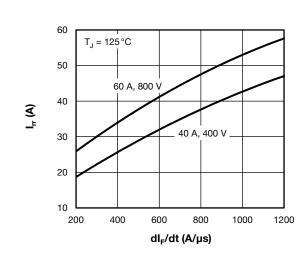


Fig. 8 - Typical Recovery Current vs. dl<sub>F</sub>/dt

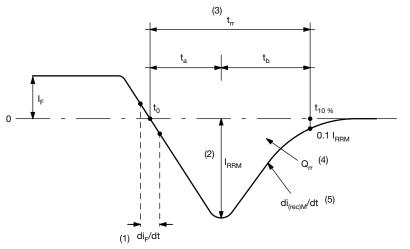


Fig. 9 - Reverse Recovery Waveform and Definitions

#### Notes

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- $^{(1)}~di_{F}/dt$  rate of change of current through zero crossing
- <sup>(2)</sup> I<sub>RRM</sub> peak reverse recovery current
- (3)  $t_{rr}$  reverse recovery time measured from  $t_0$ , crossing point of negative going I<sub>F</sub>, to point  $t_{10\%}$ , 0.1 I<sub>RRM</sub>
- $^{(4)}~~Q_{rr}$  area under curve defined by  $t_0$  and  $t_{10~\%}$

$$Q_{rr} = \int_{t_0}^{t_{10}\%} I(t)dt$$

 $^{(5)}$  di\_{(rec)}M/dt - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

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## **ORDERING INFORMATION TABLE**

Device code	VS-	E	5	Р	x	60	12	L	н	N3		
	1	2	3	4	5	6	7	8	9	10		
	1	1 - Vishay Semiconductors product										
	2	- Circ	uit conf	iguratior	า:							
		E = single diode, 2 pins										
	3	- FRED Pt Gen 5										
	4	- P=	TO-247	' packag	e							
	5	- Pro	cess typ	be:								
		X =	hyperfa	st recov	/ery							
	6	- Cur	rent rati	ng (60 =	= 60 A)							
	7	- Vol	Voltage rating (12 = 1200 V)									
	8	- L=	L = long lead									
	9	- H = AEC-Q101 qualified										
	10	- Env	ironmer	ntal digit:	:							
		N3 :	= haloge	en-free,	RoHS-c	ompliar	nt, and t	otally le	ad (Pb)	-free		

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-E5PX6012LHN3	25	500	Antistatic plastic tube					

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95536					
Part marking information	www.vishay.com/doc?95648					
SPICE model	www.vishay.com/doc?96556					



**Vishay Semiconductors** 

**TO-247AD 2L** 

### **DIMENSIONS** in millimeters and inches



Section C - C, D - D

(b, b2)

(4)

View	<u>/ B</u>

SYMBOL	MILLIN	IETERS	INC	HES	NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	STMDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209		E	15.29	15.87	0.602	0.625	3
A1	2.21	2.59	0.087	0.102		E1	13.46	-	0.53	-	
A2	1.50	2.49	0.059	0.098		е	5.46	BSC	0.215	5 BSC	
b	0.99	1.40	0.039	0.055		ØК	0.2	254	0.0	010	
b1	0.99	1.35	0.039	0.053		L	19.81	20.32	0.780	0.800	
b2	1.65	2.39	0.065	0.094		L1	3.71	4.29	0.146	0.169	
b3	1.65	2.34	0.065	0.092		ØР	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035		Ø P1	-	6.98	-	0.275	
c1	0.38	0.84	0.015	0.033		Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3	R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4	S	5.51	BSC	0.217	' BSC	
D2	0.51	1.35	0.020	0.053			•		•		•

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

(5) Lead finish uncontrolled in L1

<sup>(6)</sup> Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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